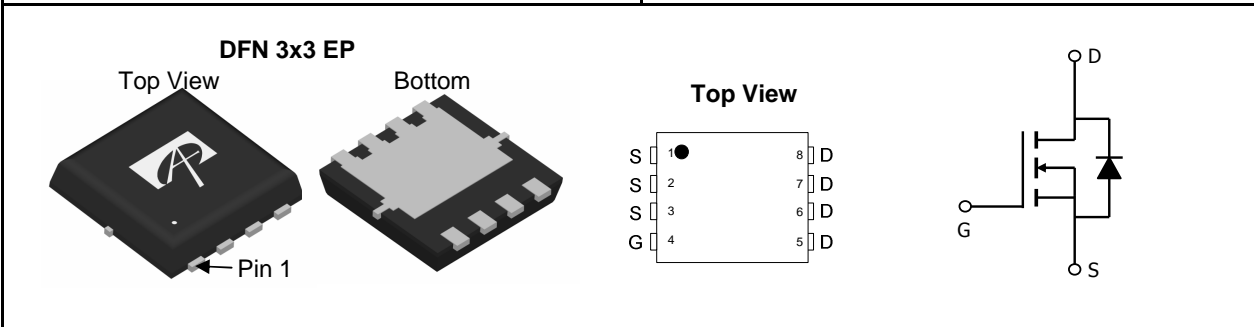




AON7430
30V N-Channel MOSFET

| General Description | Features |
|--|--|
| <p>The AON7430 uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for high side switch in SMPS and general purpose applications.</p> | <p> $V_{DS} (V) = 30V$ $I_D = 34A$ ($V_{GS} = 10V$) $R_{DS(ON)} < 12m\Omega$ ($V_{GS} = 10V$) $R_{DS(ON)} < 16m\Omega$ ($V_{GS} = 4.5V$) </p> <p> 100% UIS Tested 100% R_g Tested </p> |



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|----------------|-------------------|------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | $T_C=25^\circ C$ | 34 |
| | | $T_C=100^\circ C$ | 21 |
| Pulsed Drain Current ^C | I_{DM} | 80 | A |
| Continuous Drain Current ^A | I_{DSM} | $T_A=25^\circ C$ | 13 |
| | | $T_A=70^\circ C$ | 10.2 |
| Avalanche Current ^C | I_{AR} | 22 | A |
| Repetitive avalanche energy $L=0.1mH$ ^C | E_{AR} | 24 | mJ |
| Power Dissipation ^B | P_D | $T_C=25^\circ C$ | 23 |
| | | $T_C=100^\circ C$ | 9 |
| Power Dissipation ^A | P_{DSM} | $T_A=25^\circ C$ | 3.1 |
| | | $T_A=70^\circ C$ | 2 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ C$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|--------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | $t \leq 10s$ | 30 | 40 |
| | | Steady-State | 60 | 75 |
| Maximum Junction-to-Case ^B | $R_{\theta JC}$ | 4.5 | 5.4 | $^\circ C/W$ |

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|--|----------|----------|------------------|
| STATIC PARAMETERS | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$ | 30 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$ | | | 1 5 | μA |
| I_{GSS} | Gate-Body leakage current | $V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$ | | | 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$ | 1.5 | 1.9 | 2.5 | V |
| $I_{D(ON)}$ | On state drain current | $V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$ | 80 | | | A |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}=10\text{V}$, $I_D=20\text{A}$ $T_J=125^\circ\text{C}$ | | 10 16 | 12 19 | $\text{m}\Omega$ |
| | | $V_{GS}=4.5\text{V}$, $I_D=20\text{A}$ | | 13 | 16 | $\text{m}\Omega$ |
| g_{FS} | Forward Transconductance | $V_{DS}=5\text{V}$, $I_D=20\text{A}$ | | 45 | | S |
| V_{SD} | Diode Forward Voltage | $I_S=1\text{A}$, $V_{GS}=0\text{V}$ | | 0.7 | 1 | V |
| I_S | Maximum Body-Diode Continuous Current | | | | 25 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C_{iss} | Input Capacitance | $V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$ | 610 | 760 | 910 | pF |
| C_{oss} | Output Capacitance | | 88 | 125 | 160 | pF |
| C_{rss} | Reverse Transfer Capacitance | | 40 | 70 | 100 | pF |
| R_g | Gate resistance | $V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$ | 0.8 | 1.6 | 2.4 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| $Q_g(10\text{V})$ | Total Gate Charge | $V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=20\text{A}$ | 11 | 14 | 17 | nC |
| $Q_g(4.5\text{V})$ | Total Gate Charge | | 5 | 6.6 | 8 | nC |
| Q_{gs} | Gate Source Charge | | 1.9 | 2.4 | 2.9 | nC |
| Q_{gd} | Gate Drain Charge | | 1.8 | 3 | 4.2 | nC |
| $t_{D(on)}$ | Turn-On DelayTime | $V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=0.75\Omega$, $R_{GEN}=3\Omega$ | | 4.4 | | ns |
| t_r | Turn-On Rise Time | | | 9 | | ns |
| $t_{D(off)}$ | Turn-Off DelayTime | | | 17 | | ns |
| t_f | Turn-Off Fall Time | | | 6 | | ns |
| t_{rr} | Body Diode Reverse Recovery Time | | $I_F=20\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$ | 5.6 | 7 | 8 |
| Q_{rr} | Body Diode Reverse Recovery Charge | $I_F=20\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$ | 6.4 | 8 | 9.6 | nC |

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$, $t \leq 10\text{s}$ value and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=150^\circ\text{C}$.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

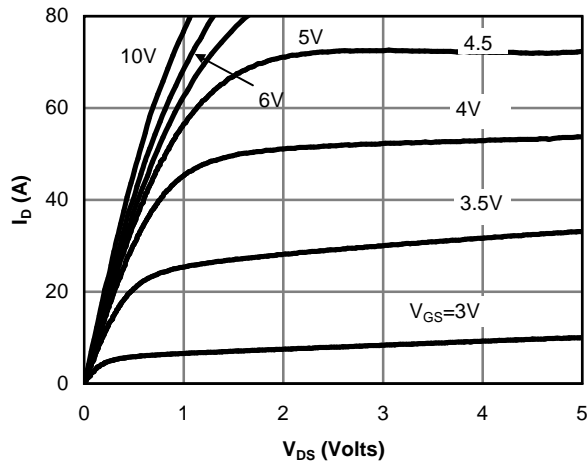


Fig 1: On-Region Characteristics

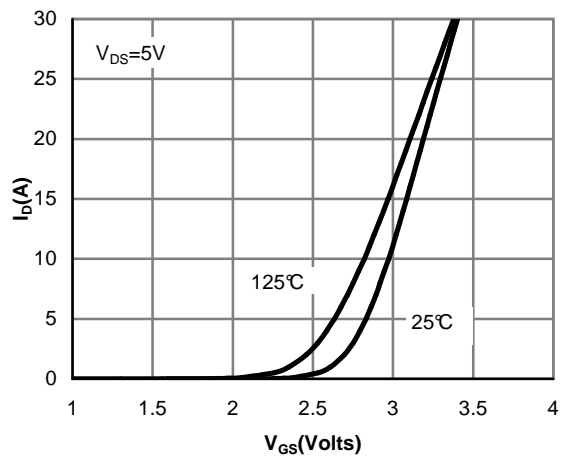


Figure 2: Transfer Characteristics

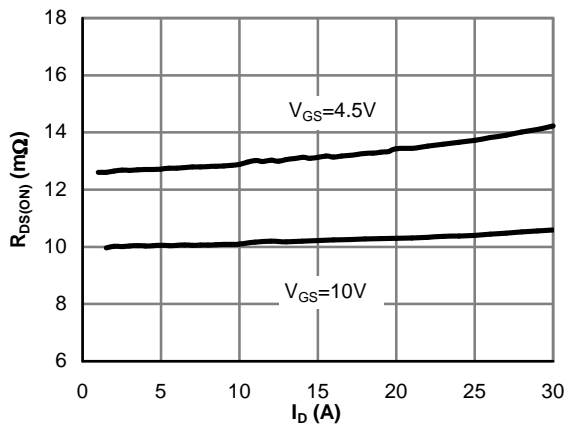


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

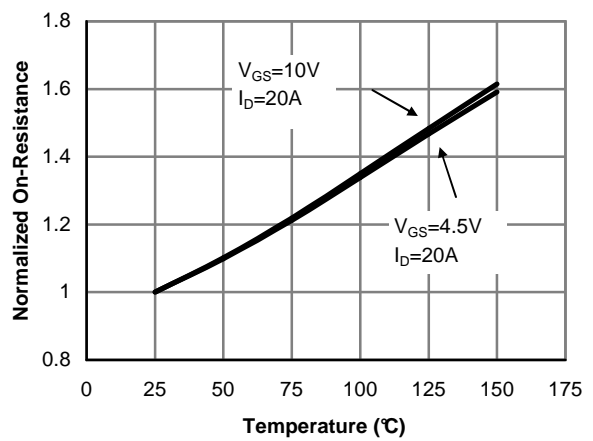


Figure 4: On-Resistance vs. Junction Temperature

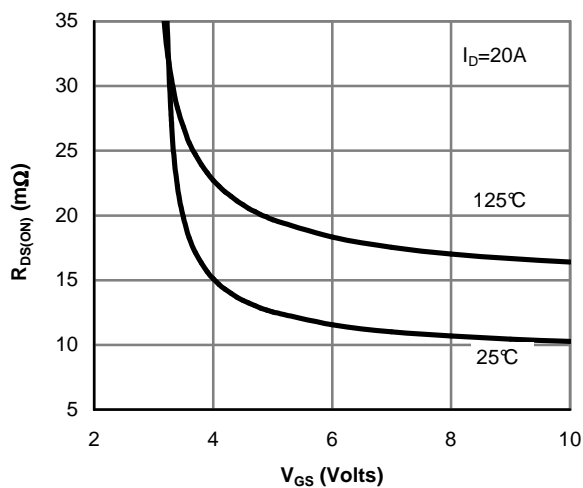


Figure 5: On-Resistance vs. Gate-Source Voltage

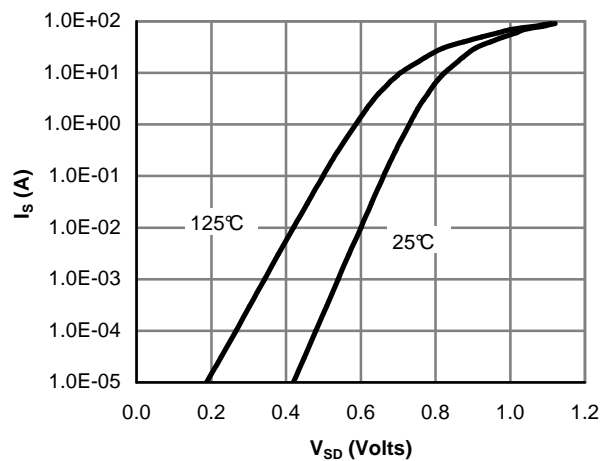


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

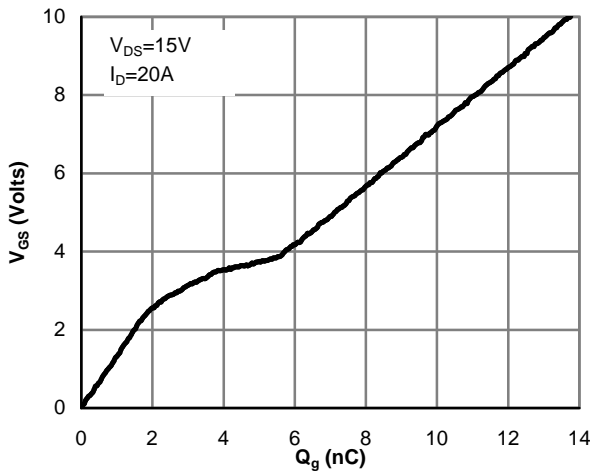


Figure 7: Gate-Charge Characteristics

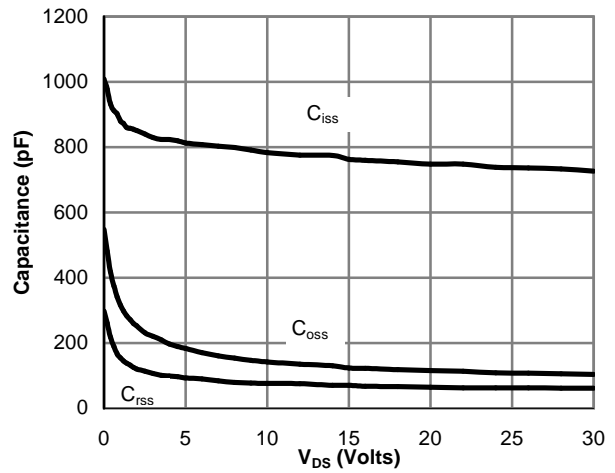


Figure 8: Capacitance Characteristics

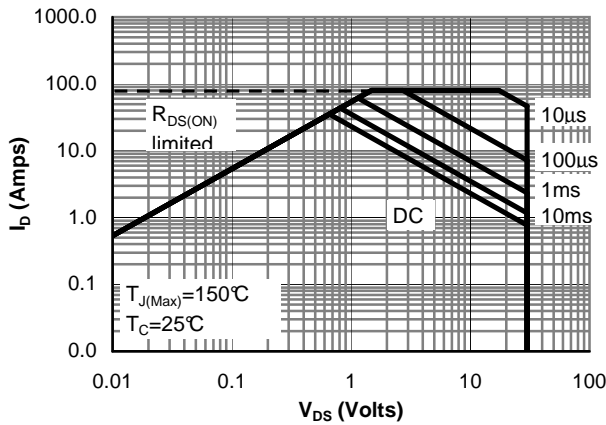


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

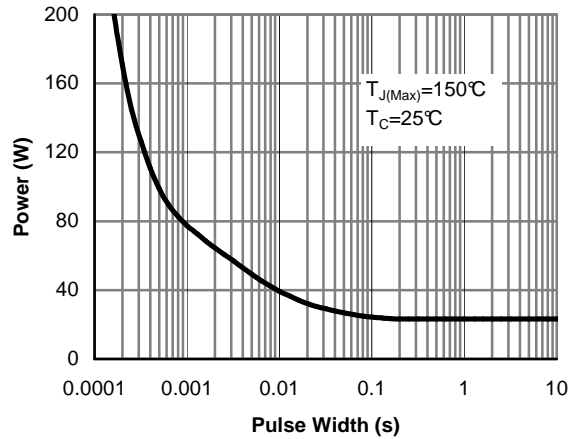


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

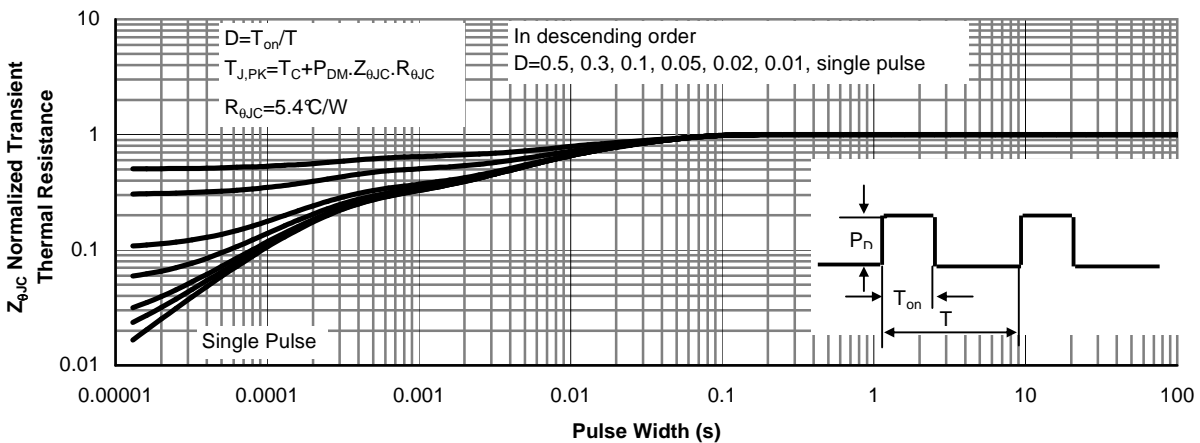


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

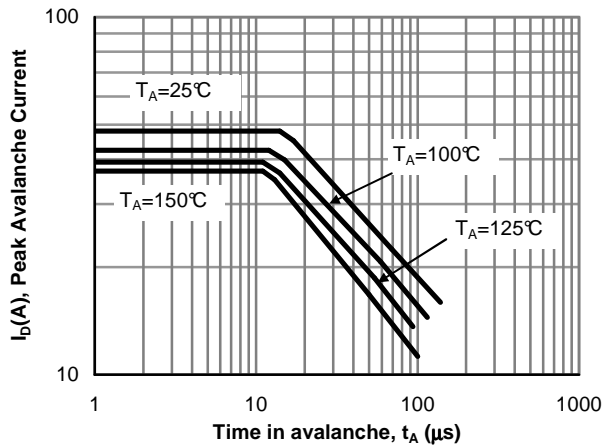


Figure 12: Single Pulse Avalanche capability (Note C)

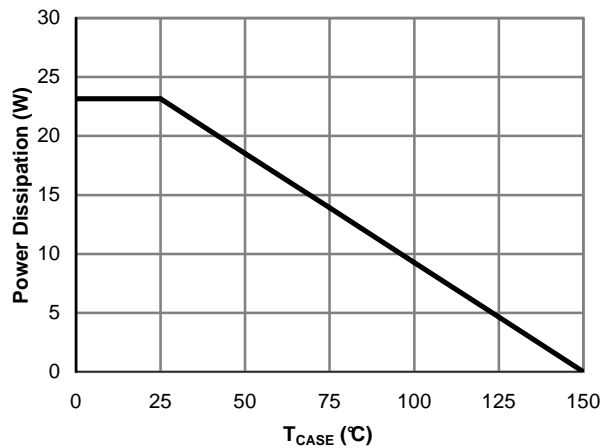


Figure 13: Power De-rating (Note F)

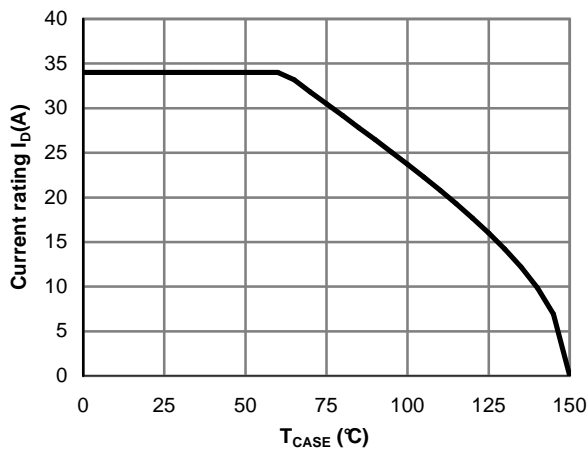


Figure 14: Current De-rating (Note F)

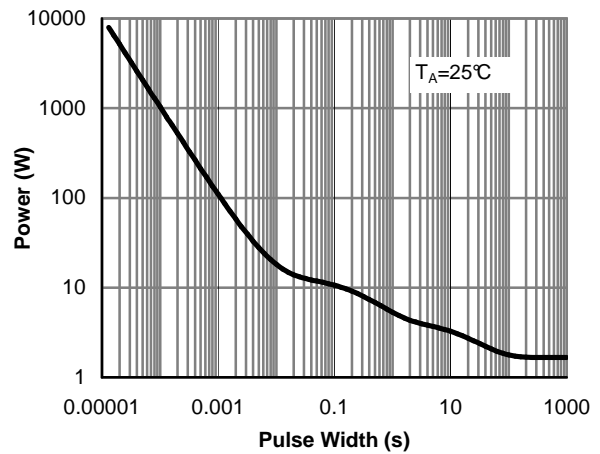


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

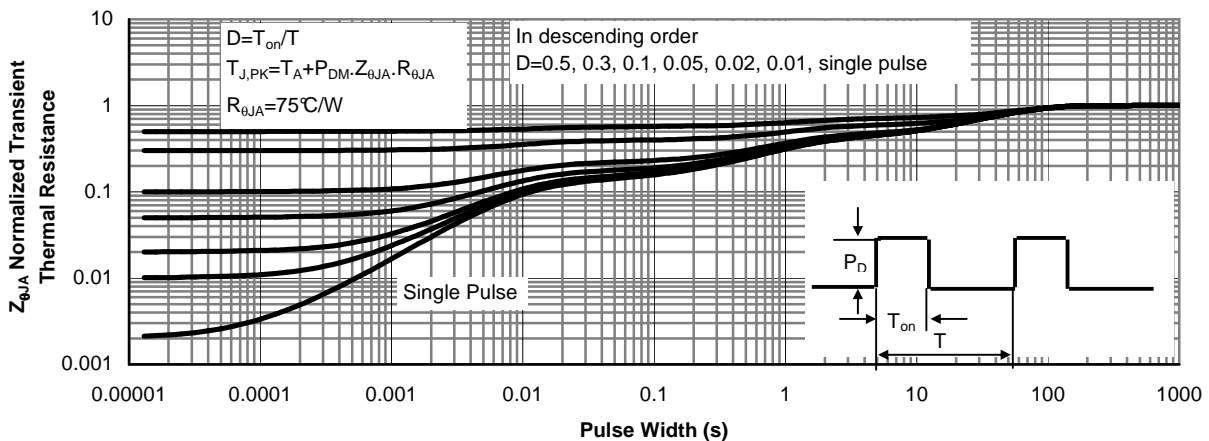
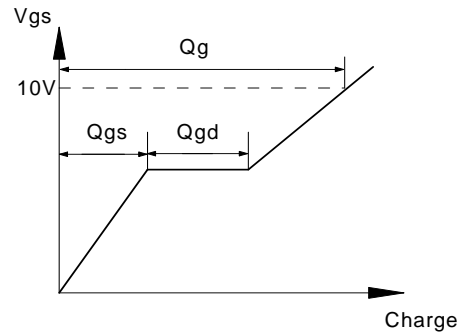
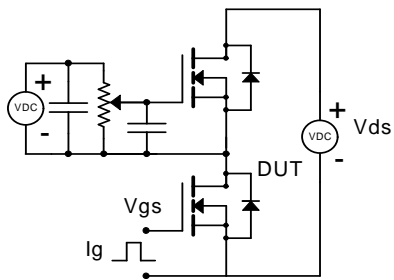
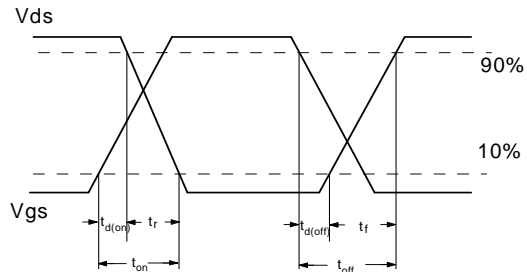
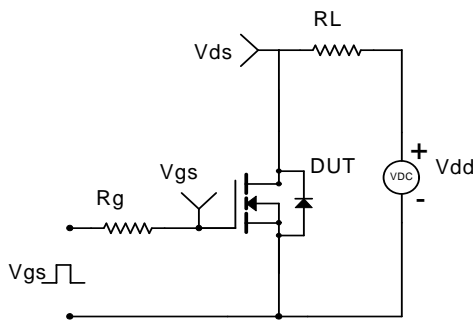


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

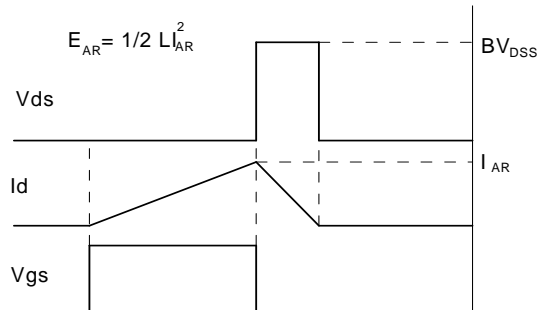
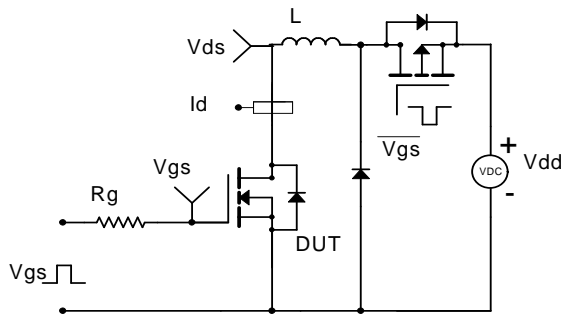
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

